

T2N4401

Low Power Bipolar Transistors

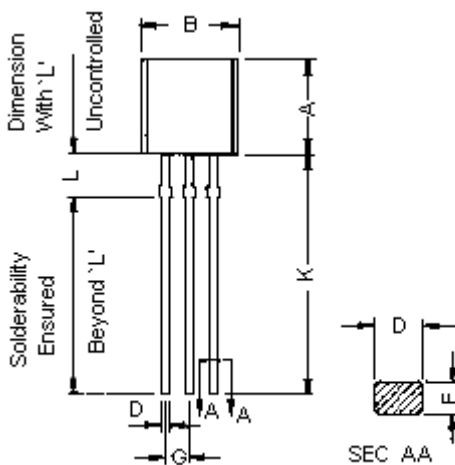


Features:

- NPN Silicon Planar Epitaxial Transistors.
- General purpose Switching Applications.

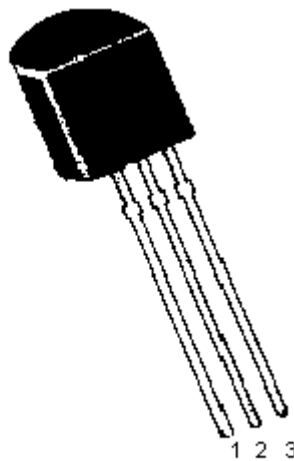
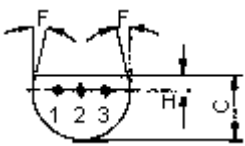


TO-92 Plastic Package



Dimensions	Minimum	Maximum
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5°	
G	1.14	1.40
H		1.53
K	12.70	-
L	1.982	2.082

Dimensions : Millimetres



Pin Configuration
 1 = Emitter
 2 = Base
 3 = Collector



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Absolute Maximum Ratings

Rating	Symbol	T2N4401	Unit
Collector-Emitter Voltage	V_{CEO}	40	V
Collector-Base Voltage	V_{CBO}	60	
Emitter-Base Voltage	V_{EBO}	6	
Collector Current Continuous	I_C	600	mA
Power Dissipation at $T_a = 25^\circ\text{C}$ Derate above 25°C	P_D	625	mW
Power Dissipation at $T_C = 25^\circ\text{C}$ Derate above 25°C		5.0	mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$
Thermal Resistance			
Junction to Case	$R_{th(j-c)}$	83.3	$^\circ\text{C/W}$
Junction to Ambient	$R_{th(j-a)}$	200	

Electrical Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	T2N4401	Unit
Collector Emitter Voltage $I_C = 1\text{mA}, I_B = 0$	BV_{CEO}^*	>40	V
Collector Base Voltage $I_C = 100\mu\text{A}, I_E = 0$	BV_{CBO}	>60	
Emitter Base Voltage $I_E = 100\mu\text{A}, I_C = 0$	BV_{EBO}	>6	
Base Cut off Current $V_{CE} = 35\text{V}, V_{EB} = 0.4\text{V}$	I_{BEV}	<0.1	μA
Collector Cut off Current $V_{CE} = 35\text{V}, V_{EB} = 0.4\text{V}$	I_{CEX}		
Collector Emitter Saturation Voltage $I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{CE(Sat)}^*$	<0.4 <0.75	V
Base Emitter Saturation Voltage $I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{BE(Sat)}^*$	0.75 - 0.95 <1.2	

*Pulse Test : Pulse Width: $\leq 300\mu\text{s}$, Duty $\leq 2.0\%$

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Electrical Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	T2N4401	Unit
DC Current Gain $I_C = 0.1\text{mA}, V_{CE} = 1\text{V}$ $I_C = 1\text{mA}, V_{CE} = 1\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C = 150\text{mA}, V_{CE} = 1\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 2\text{V}^*$	h_{FE}	>20 >40 >80 100 - 300 >40	-
Dynamic Characteristics			
Small Signal Current Gain $I_C = 1\text{mA}, V_{CE} = 10\text{V}, f = 1\text{KHz}$	h_{fe}	40 - 500	-
Input Impedance $I_C = 1\text{mA}, V_{CE} = 10\text{V}, f = 1\text{KHz}$	h_{ie}	1.0 - 15	k Ω
Characteristic	Symbol	2N4401	Unit
Voltage Feedback Ratio $I_C = 1\text{mA}, V_{CE} = 10\text{V}, f = 1\text{KHz}$	h_{re}	0.1 - 8.0	$\times 10^{-4}$
Output Impedance $I_C = 1\text{mA}, V_{CE} = 10\text{V}, f = 1\text{KHz}$	h_{oe}	1.0 - 30	$\mu\Omega$
Collector-Base Capacitance $V_{CB} = 5\text{V}, I_E = 0, f = 100\text{KHz}$ $V_{CB} = 10\text{V}, I_E = 0, f = 140\text{KHz}$	C_{cb}	<6.5 -	pF
Emitter-Base Capacitance $V_{EB} = 0.5\text{V}, I_C = 0, f = 100\text{kHz}$	C_{eb}	<30	
Transition Frequency $I_C = 20\text{mA}, V_{CE} = 10\text{V}, f = 100\text{MHz}$	f_T	>250	MHz
Switching Characteristics			
$V_{CC} = 30\text{V}, V_{EB} = 2\text{V}$ $I_C = 150\text{mA}, I_{B1} = 15\text{mA}$			
Delay Time	t_d	<15	ns
Rise Time	t_r	<20	
$V_{CC} = 30\text{V}, I_C = 150\text{mA}$ $I_{B1} = I_{B2} = 15\text{mA}$			
Storage time	t_s	<225	ns
Fall Time	t_f	<30	

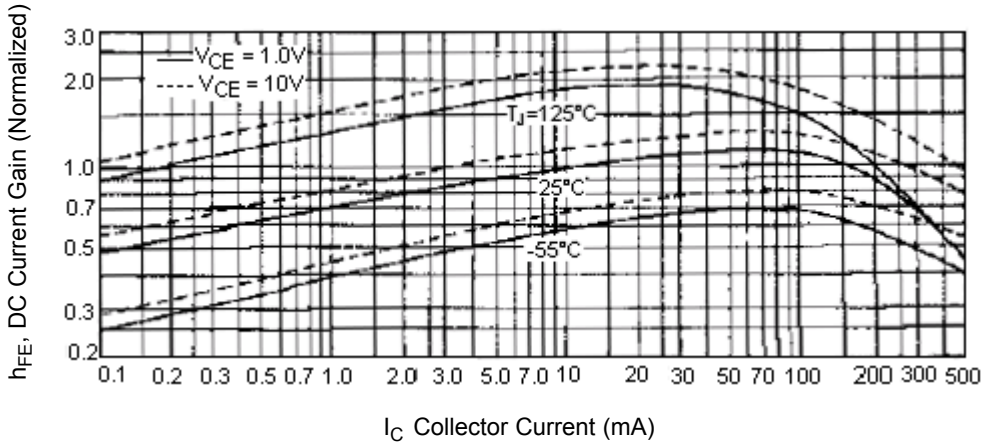
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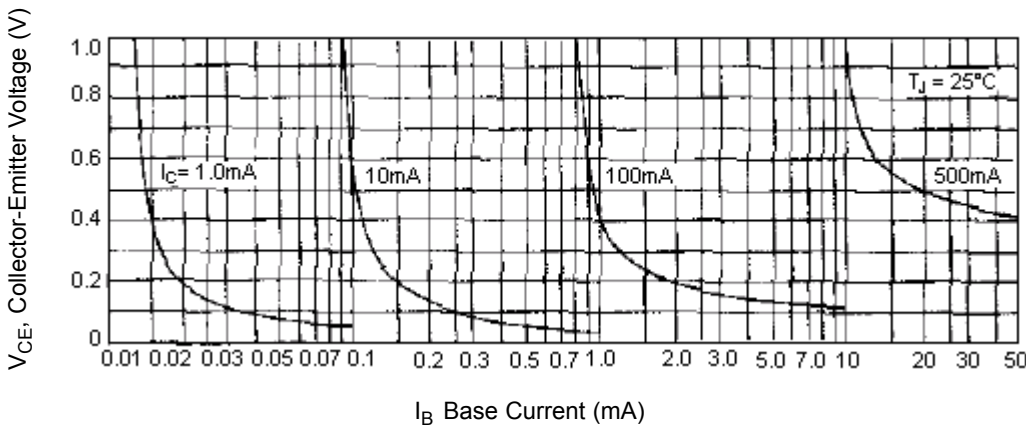
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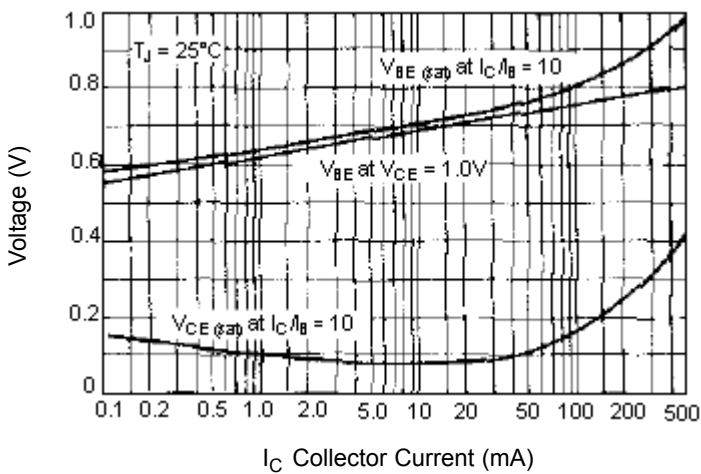
DC Current Gain



DC Current Gain



On Voltages

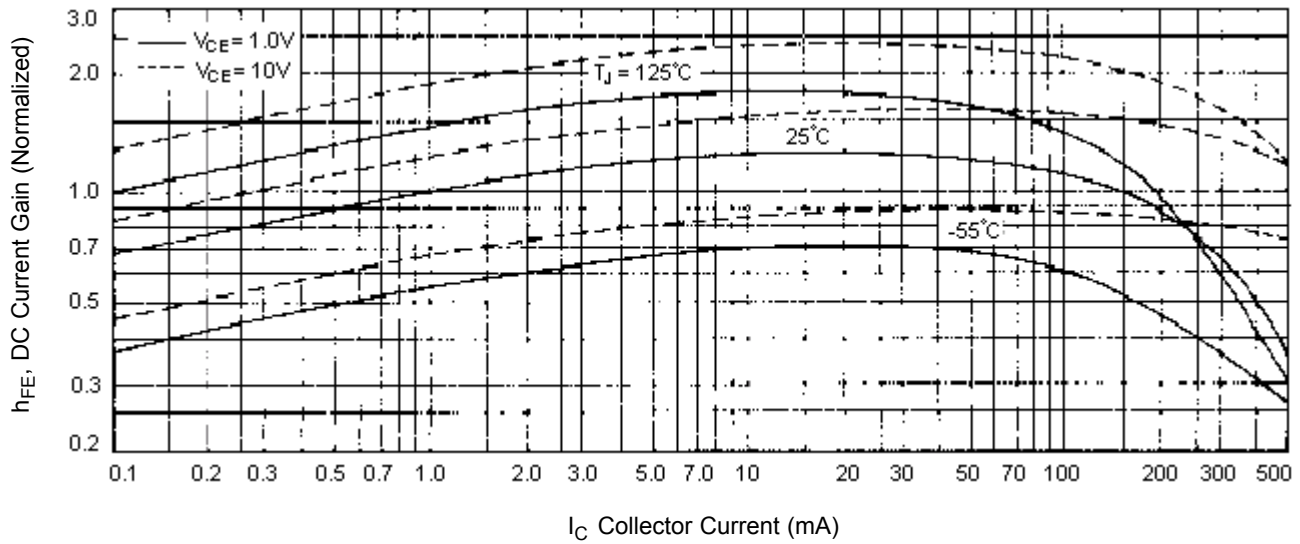


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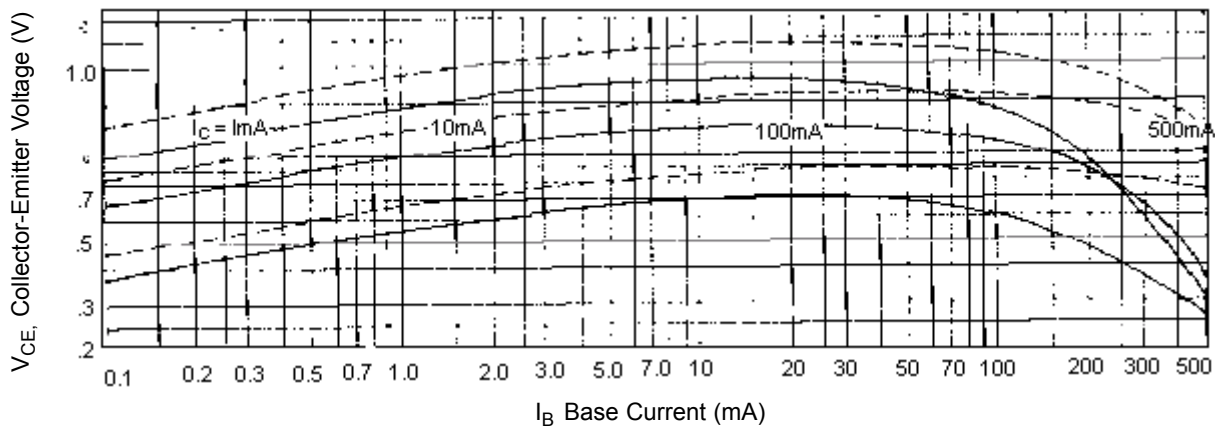
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DC Current Gain



Collector Saturation Region

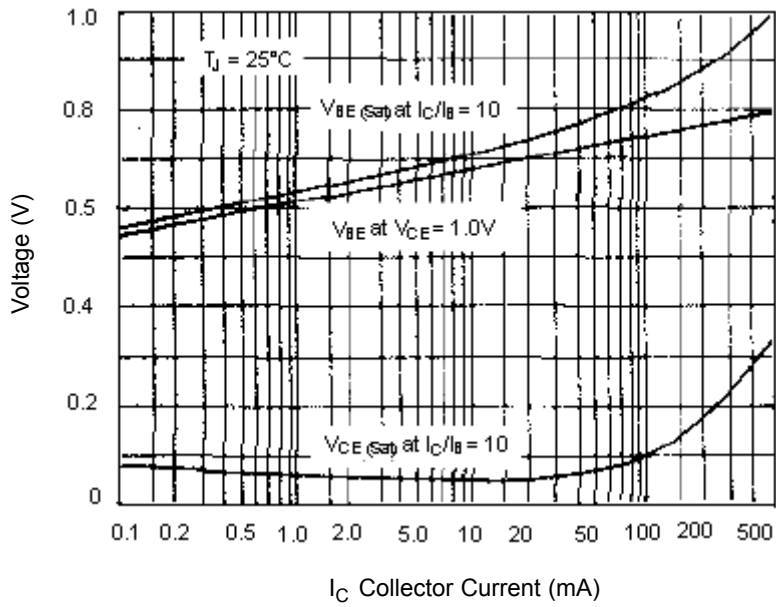


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On Voltages



Part Number Table

Package	Part Number
TO-92	2N4401